

GaAs PIN MMIC SPDT SWITCH 55 - 86 GHz

Typical Applications

This HMC-SDD112 is ideal for:

- FCC E-Band Communication Systems
- Short-Haul / High Capacity Radios
- · Automotive Radar
- Test & Measurement Equipment
- SATCOM
- Sensors

Features

Low Insertion Loss: 2 dB

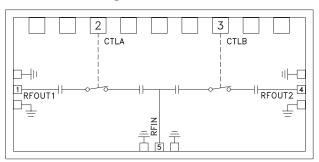
High Isolation: 30 dB

DC Blocked RF I/Os

Integrated DC Bias Circuitry

Die Size: 2.01 x 0.975 x 0.1 mm

Functional Diagram



General Description

The HMC-SDD112 is a monolithic, GaAs PIN diode based Single Pole Double Throw (SPDT) MMIC Switch which exhibits low insertion loss and high isolation. This all-shunt MMIC SPDT features on-chip DC blocks and DC bias voltage decoupling circuitry. All bond pads and the die backside are Ti/Au metallized and the PIN diode devices are fully passivated for reliable operation. The HMC-SDD112 GaAs PIN SPDT is compatible with conventional die attach methods, as well as thermocompression and thermosonic wirebonding, making it ideal for MCM and hybrid microcircuit applications. All data shown herein is measured with the chip in a 50 Ohm environment and contacted with RF probes.

Electrical Specifications*, $T_A = +25$ °C, with -5/+5V Control, 50 Ohm System

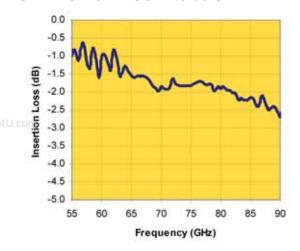
Parameter	Min.	Тур.	Max.	Units
Frequency Range	55 - 86		GHz	
Insertion Loss		2	3	dB
Isolation	25	30		dB
Return Loss ON State		12		dB
Current (+5 V) ON State		22		mA
Current (-5 V) OFF State		-63		nA

 $^{^{\}star}$ Unless otherwise indicated, all measurements are from probed die

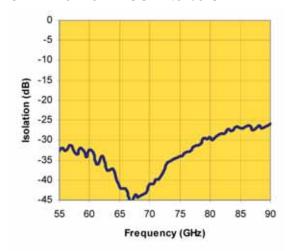


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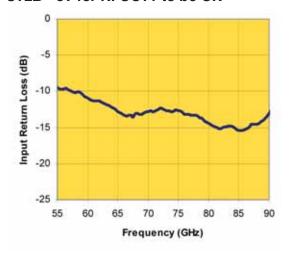
"On" Insertion Loss vs. Freq. CTLA= -5V, CTLB= 5V for RFOUT1 to be ON



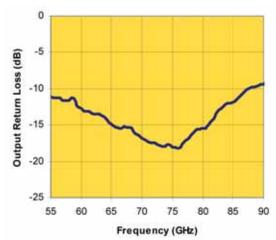
"Off" Isolation vs. Freq. CTLA= +5V, CTLB= -5V for RFOUT1 to be OFF



"On" Input Return Loss vs. Freq. CTLA= -5V, CTLB= 5V for RFOUT1 to be ON



"On" Output Return Loss vs. Freq.
CTLA= -5V, CTLB= 5V for RFOUT1 to be ON



Note 1: Measured Performance Characteristics (Typical Performance at 25°C) Test data is taken with probes on RFIN and RFOUT1 with RFOUT2 left open.



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Absolute Maximum Ratings

Bias Voltage Range	-5.5 to 5.5 Vdc	
Storage Temperature	-65 to +150 °C	
Operating Temperature	-55 to +85 °C	
Bias Current (ON State)	30 mA	

ELECTROSTATIC SENSITIVE DEVICE OBSERVE HANDLING PRECAUTIONS

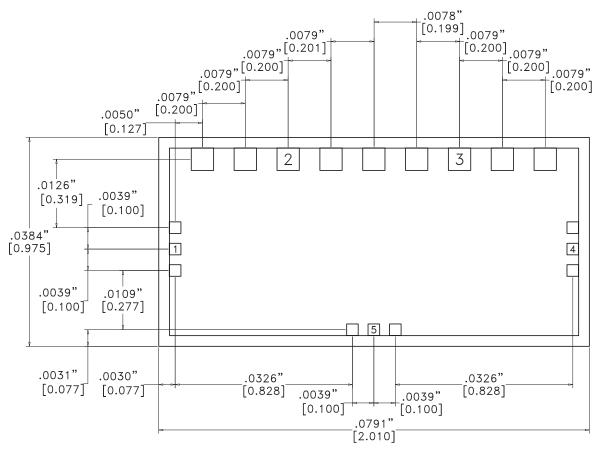
Control Voltages

U.	State	Bias Condition	
	Low	-5 V @ 63 nA typical	
	High	+5 V @ 22 mA typical	

Truth Table

Contro	l Input	Signal Path State		
CTLA	CTLB	RFIN to RFOUT1	RFIN to RFOUT2	
Low (-5V) High (+5V)	High (+5V) Low (-5V)	On Off	Off On	

Outline Drawing



NOTES:

- 1. ALL DIMENSIONS ARE IN INCHES [MM].
- 2. TYPICAL BOND PAD IS .004" SQUARE.
- 3. BACKSIDE METALLIZATION: GOLD.
- 4. BACKSIDE METAL IS GROUND.
- 5. BOND PAD METALLIZATION: GOLD.
- 6. CONNECTION NOT REQUIRED FOR UNLABELED BOND PADS.
- 7. OVERALL DIE SIZE ±.002"